

Silicon PNP Power Transistors

2SA1147

DESCRIPTION

- With TO-3 package
- High power dissipations
- Complement to type 2SC2707

APPLICATIONS

- For power switching amplifier and general purpose applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

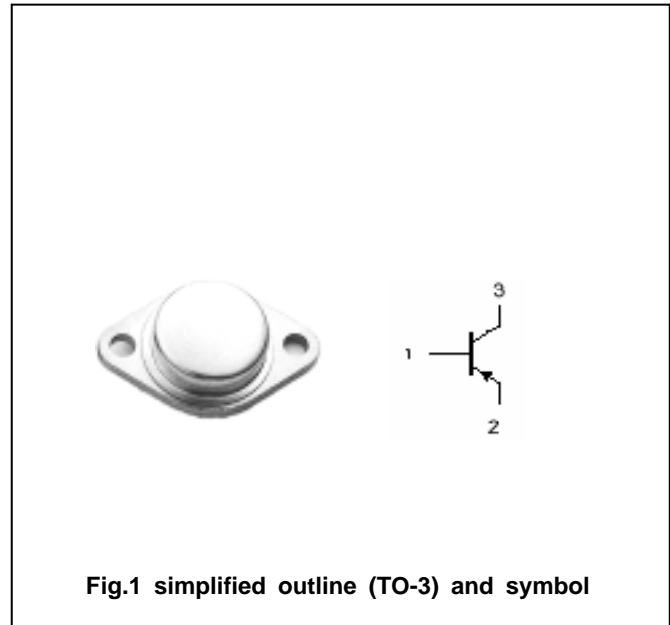


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings($T_a =$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-180	V
V_{CEO}	Collector-emitter voltage	Open base	-180	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-15	A
I_B	Base current		-5	A
P_C	Collector power dissipation	$T_C=25$	150	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-65~150	

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CHARACTERISTICS

 $T_j=25$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-50mA ; I_B=0$	-180			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=-1mA ; I_E=0$	-180			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=-1mA ; I_C=0$	-5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-10A ; I_B=-1A$			-3.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=-180V ; I_E=0$			-0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=-6V ; I_C=0$			-0.1	mA
h_{FE}	DC current gain	$I_C=-5A ; V_{CE}=-4V$	30			
f_T	Transition frequency	$I_C=-0.5A ; V_{CE}=-12V$		60		MHz

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PACKAGE OUTLINE



Fig.2 outline dimensions (unindicated tolerance: $\pm 0.1\text{mm}$)